

MOSFETs Silicon N-channel MOS (U-MOS IV)

# **TK75A06K3**

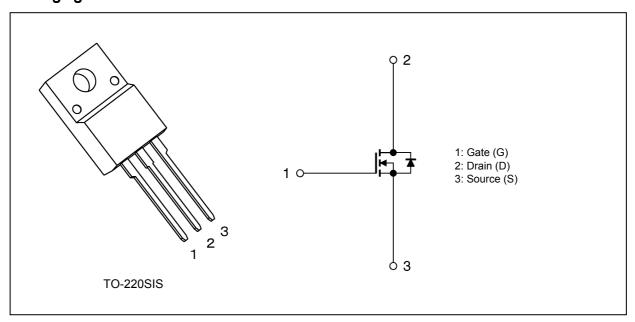
#### 1. Applications

• Switching Voltage Regulators

#### 2. Features

- (1) Low drain-source on-resistance:  $R_{DS(ON)} = 4.5 \text{ m}\Omega$  (typ.)
- (2) Low leakage current:  $I_{DSS} = 10 \mu A \text{ (max) (V}_{DS} = 60 \text{ V)}$
- (3) Enhancement mode:  $V_{th}$  = 3.0 to 4.0 V ( $V_{DS}$  = 10 V,  $I_{D}$  = 1 mA)

#### 3. Packaging and Internal Circuit



### 4. Absolute Maximum Ratings (Note) (Ta = 25°C unless otherwise specified)

| Characteristics                         | Symbol   | Rating           | Unit       |    |
|---|----------|------------------|------------|----|
| Drain-source voltage                    |          | V <sub>DSS</sub> | 60         | V  |
| Gate-source voltage                     |          | $V_{GSS}$        | ±20        |    |
| Drain current (DC)                      | (Note 1) | I <sub>D</sub>   | 75         | Α  |
| Drain current (pulsed)                  | (Note 1) | I <sub>DP</sub>  | 225        |    |
| Power dissipation $(T_c = 25^{\circ}C)$ |          | $P_{D}$          | 35         | W  |
| Single-pulse avalanche energy           | (Note 2) | E <sub>AS</sub>  | 103        | mJ |
| Avalanche current                       |          | I <sub>AR</sub>  | 75         | Α  |
| Channel temperature                     |          | T <sub>ch</sub>  | 150        | ů  |
| Storage temperature                     |          | T <sub>stg</sub> | -55 to 150 |    |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).



#### 5. Thermal Characteristics

| Characteristics                       | Symbol                | Max  | Unit |
|---------------------------------------|-----------------------|------|------|
| Channel-to-case thermal resistance    | R <sub>th(ch-c)</sub> | 3.57 | °C/W |
| Channel-to-ambient thermal resistance | R <sub>th(ch-a)</sub> | 62.5 |      |

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2:  $V_{DD}$  = 25 V,  $T_{ch}$  = 25°C (initial), L = 25.1  $\mu H$ ,  $R_G$  = 1  $\Omega$ ,  $I_{AR}$  = 75 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



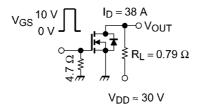
#### 6. Electrical Characteristics

### 6.1. Static Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

| Characteristics                | Symbol               | Test Condition                                    | Min | Тур. | Max | Unit |
|--------------------------------|----------------------|---|-----|------|-----|------|
| Gate leakage current           | I <sub>GSS</sub>     | $V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$ | _   | _    | ±1  | μА   |
| Drain cut-off current          | I <sub>DSS</sub>     | V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V     | _   | _    | 10  |      |
| Drain-source breakdown voltage | V <sub>(BR)DSS</sub> | I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V     | 60  | _    | _   | V    |
|                                | V <sub>(BR)DSX</sub> | I <sub>D</sub> = 10 mA, V <sub>GS</sub> = -20 V   | 35  | _    | _   |      |
| Gate threshold voltage         | $V_{th}$             | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA     | 3.0 | _    | 4.0 |      |
| Drain-source on-resistance     | R <sub>DS(ON)</sub>  | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 38 A     | _   | 4.5  | 5.5 | mΩ   |

### 6.2. Dynamic Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

| Characteristics                | Symbol           | Test Condition   | Min | Тур. | Max | Unit |
|--------------------------------|------------------|--|-----|------|-----|------|
| Input capacitance              | C <sub>iss</sub> | V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz | _   | 4500 | _   | pF   |
| Reverse transfer capacitance   | C <sub>rss</sub> |  | _   | 600  |     |      |
| Output capacitance             | C <sub>oss</sub> |  | _   | 800  | _   |      |
| Switching time (rise time)     | t <sub>r</sub>   | See Figure 6.2.1.  | _   | 25   | _   | ns   |
| Switching time (turn-on time)  | t <sub>on</sub>  |  | _   | 54   | _   |      |
| Switching time (fall time)     | t <sub>f</sub>   |  | _   | 27   | _   |      |
| Switching time (turn-off time) | t <sub>off</sub> |  | _   | 74   |     |      |



Duty  $\leq$  1%,  $t_W=10~\mu s$ 

Fig. 6.2.1 Switching Time Test Circuit

### 6.3. Gate Charge Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

| Characteristics                                 | Symbol           | Test Condition   | Min | Тур. | Max | Unit |
|---|------------------|--|-----|------|-----|------|
| Total gate charge (gate-source plus gate-drain) | Qg               | $V_{DD} \approx 48 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 75 \text{ A}$ | _   | 85   | _   | nC   |
| Gate-source charge 1                            | Q <sub>gs1</sub> |  | _   | 24   | _   |      |
| Gate-drain charge                               | Q <sub>gd</sub>  |  | _   | 35   | _   |      |

#### 6.4. Source-Drain Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

| Characteristics                |          | Symbol           | Test Condition                                | Min | Тур. | Max  | Unit |
|--------------------------------|----------|------------------|---|-----|------|------|------|
| Reverse drain current (DC)     | (Note 1) | I <sub>DR</sub>  | _   | _   | _    | 75   | Α    |
| Reverse drain current (pulsed) | (Note 1) | I <sub>DRP</sub> | _   | _   | _    | 225  |      |
| Diode forward voltage          |          | V <sub>DSF</sub> | I <sub>DR</sub> = 75 A, V <sub>GS</sub> = 0 V | _   | _    | -1.2 | V    |
| Reverse recovery time          |          | t <sub>rr</sub>  | I <sub>DR</sub> = 75 A, V <sub>GS</sub> = 0 V | _   | 49   | _    | ns   |
| Reverse recovery charge        |          | Q <sub>rr</sub>  | -dl <sub>DR</sub> /dt = 100 A/μs              | _   | 76   | _    | nC   |



### 7. Marking (Note)

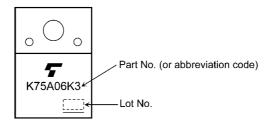


Fig. 7.1 Marking

Note: A line under a Lot No. identifies the indication of product Labels.

Not underlined: [[Pb]]/INCLUDES > MCV

Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product.

The RoHS is the Directive 2002/95/EC of the European Parliament and of the Council of 27 January 2003 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

#### 8. Characteristics Curves (Note)

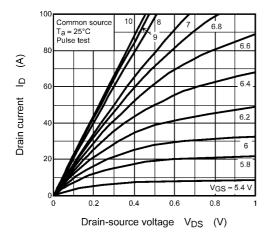


Fig. 8.1 I<sub>D</sub> - V<sub>DS</sub>

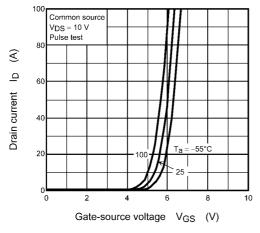


Fig. 8.3 I<sub>D</sub> - V<sub>GS</sub>

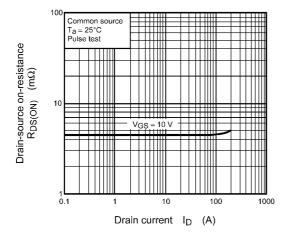


Fig. 8.5 R<sub>DS(ON)</sub> - I<sub>D</sub>

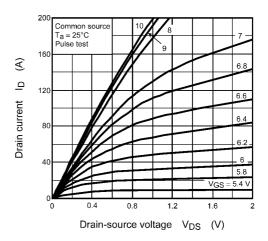


Fig. 8.2 I<sub>D</sub> - V<sub>DS</sub>

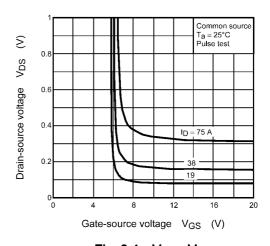


Fig. 8.4  $V_{DS}$  -  $V_{GS}$ 

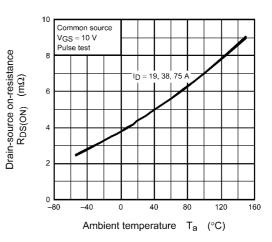


Fig. 8.6 R<sub>DS(ON)</sub> - T<sub>a</sub>

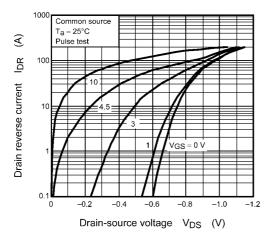


Fig. 8.7 IDR - VDS

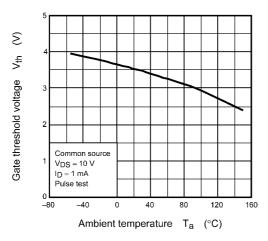


Fig. 8.9 V<sub>th</sub> - T<sub>a</sub>

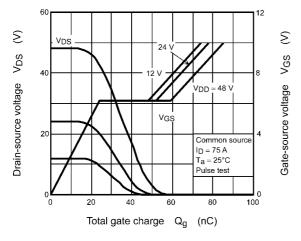


Fig. 8.11 Dynamic Input/Output Characteristics

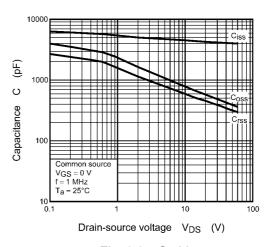
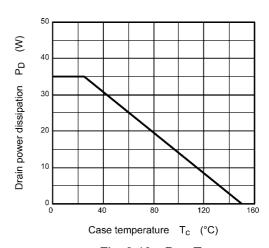


Fig. 8.8 C - V<sub>DS</sub>



 $\label{eq:Fig. 8.10} \begin{array}{ll} \text{Fig. 8.10} & \text{P}_{\text{D}} \text{-} \text{T}_{\text{C}} \\ \text{(Guaranteed Maximum)} \end{array}$ 

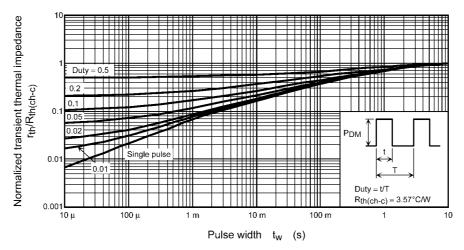


Fig. 8.12  $r_{th}/R_{th(ch-c)} - t_w$  (Guaranteed Maximum)

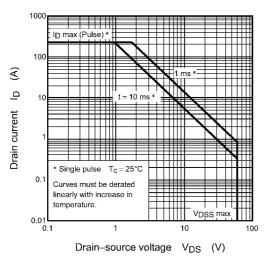


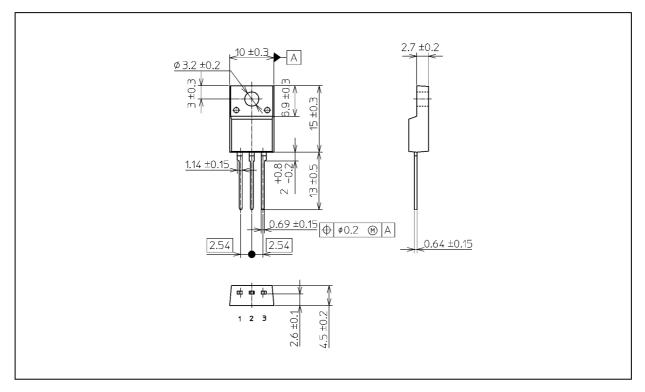
Fig. 8.13 Safe Operating Area (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



## **Package Dimensions**

Unit: mm



Weight: 1.7 g (typ.)

|                     | Package Name(s) |
|---------------------|-----------------|
| JEITA: SC-67        |                 |
| TOSHIBA: 2-10U1S    |                 |
| Nickname: TO-220SIS |                 |



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